

/ Descriptions

TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

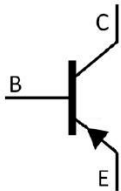
/ Features

， 3DA4793
High transition frequency, complementary to 3DA4793.

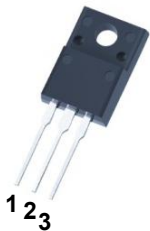
/ Applications

Power amplifier, driver stage amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

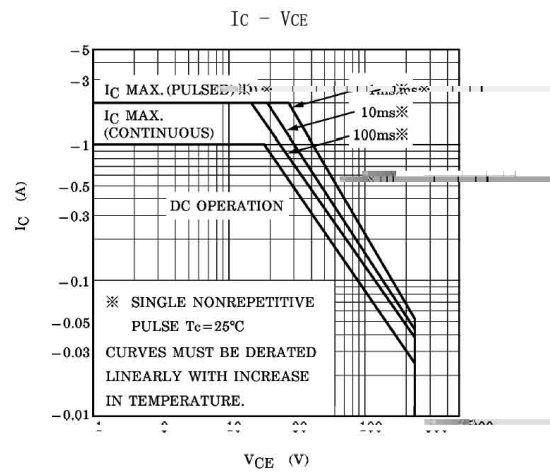
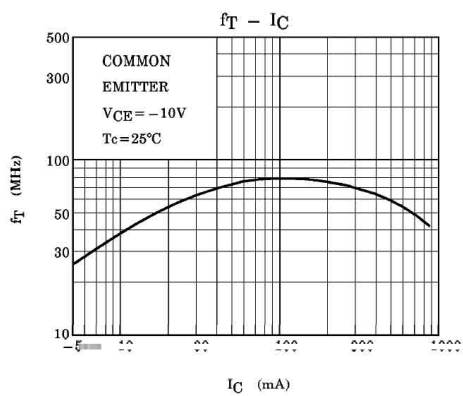
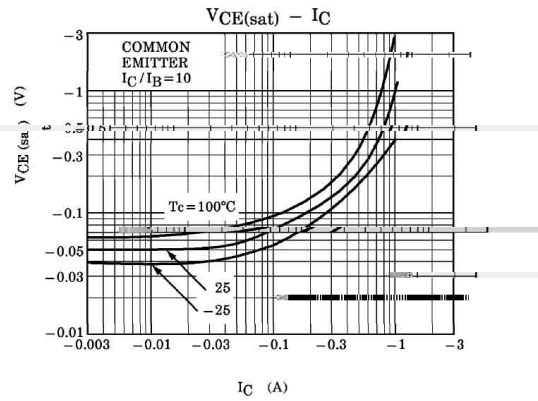
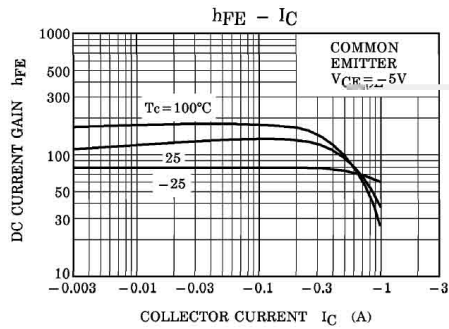
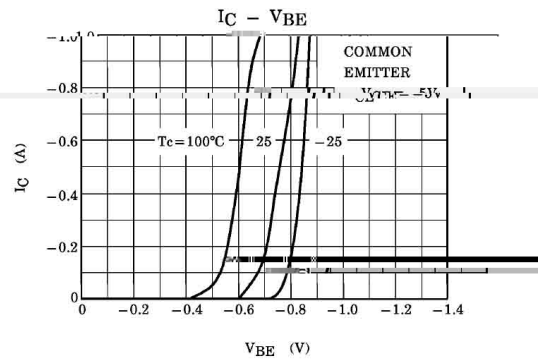
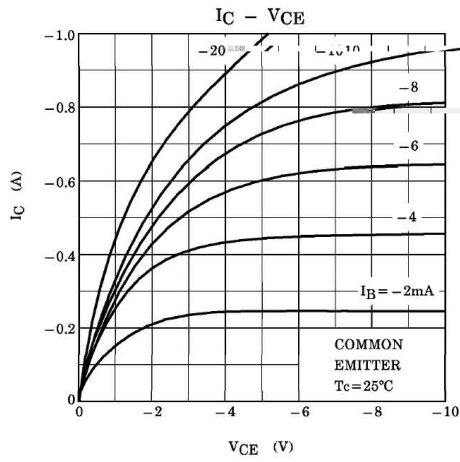
/ h_{FE} Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-230	V
Collector to Emitter Voltage	V_{CEO}	-230	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.0	A
Base Current	I_B	-0.1	A
Collector Power Dissipation	P_C	2.0	W
	$P_{C(T_c=25^\circ C)}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

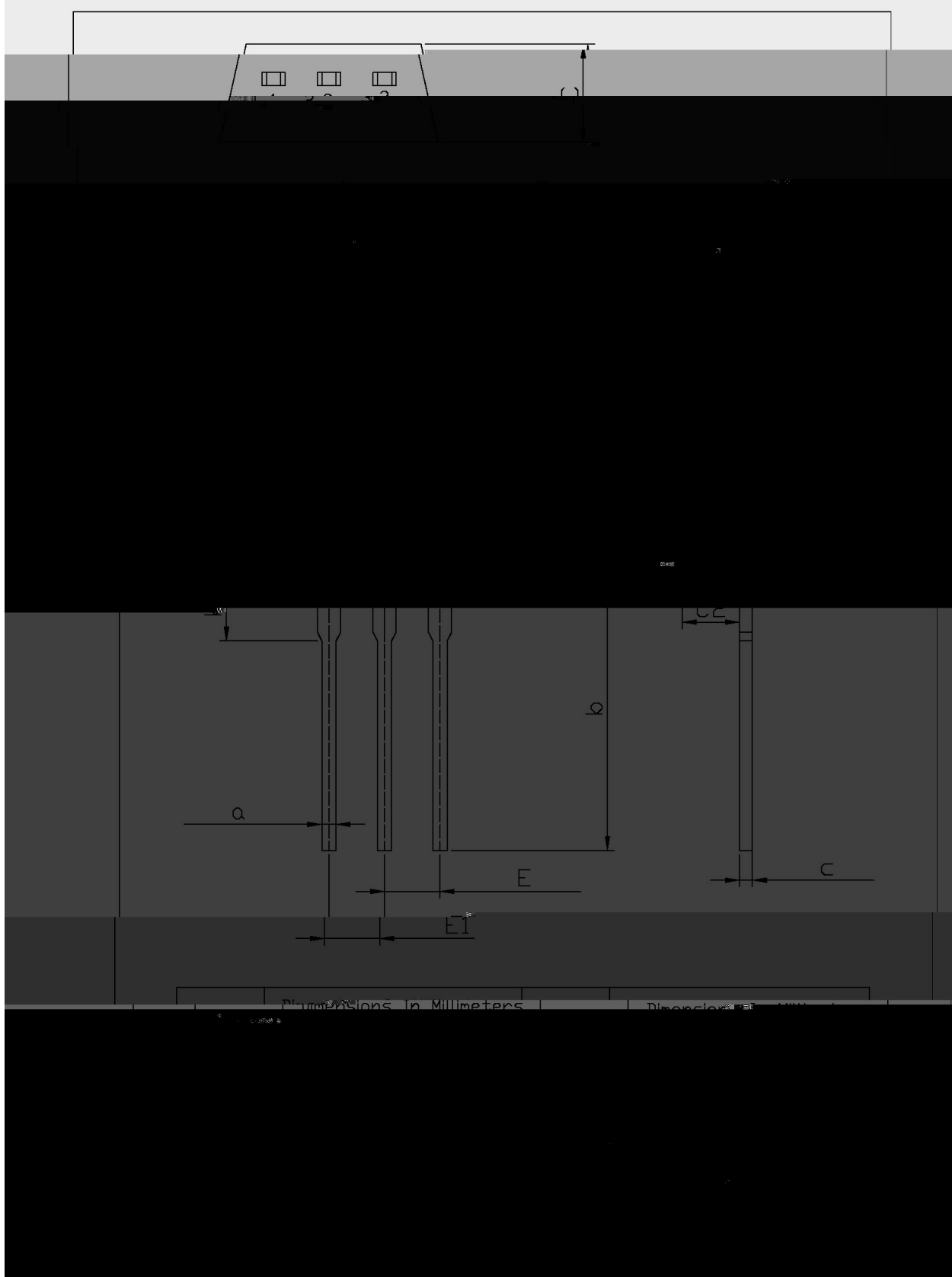
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10mA$ $I_B = 0$	-230			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -230V$ $I_E = 0$			-1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = -5.0V$ $I_C = 0$			-1.0	μA

/ **Electrical Characteristic Curve**

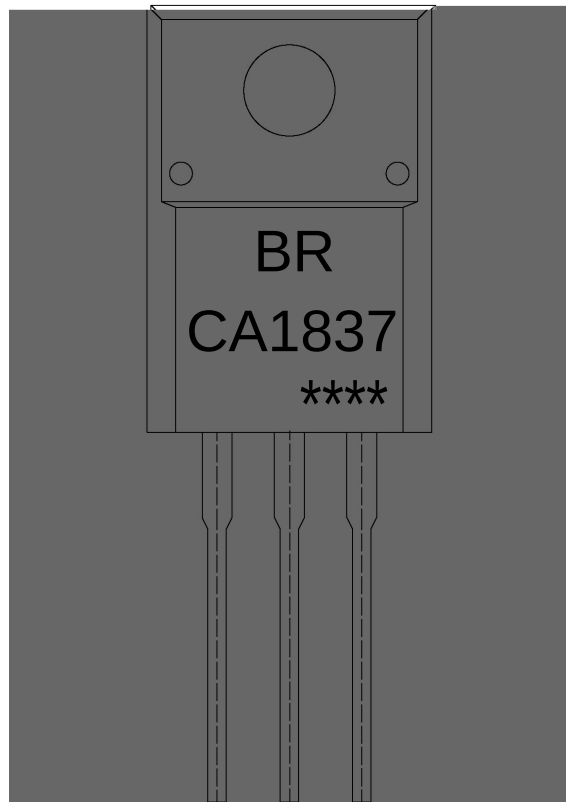


T0-220F

单位: 



/ **Marking Instructions**



BR

CA1837

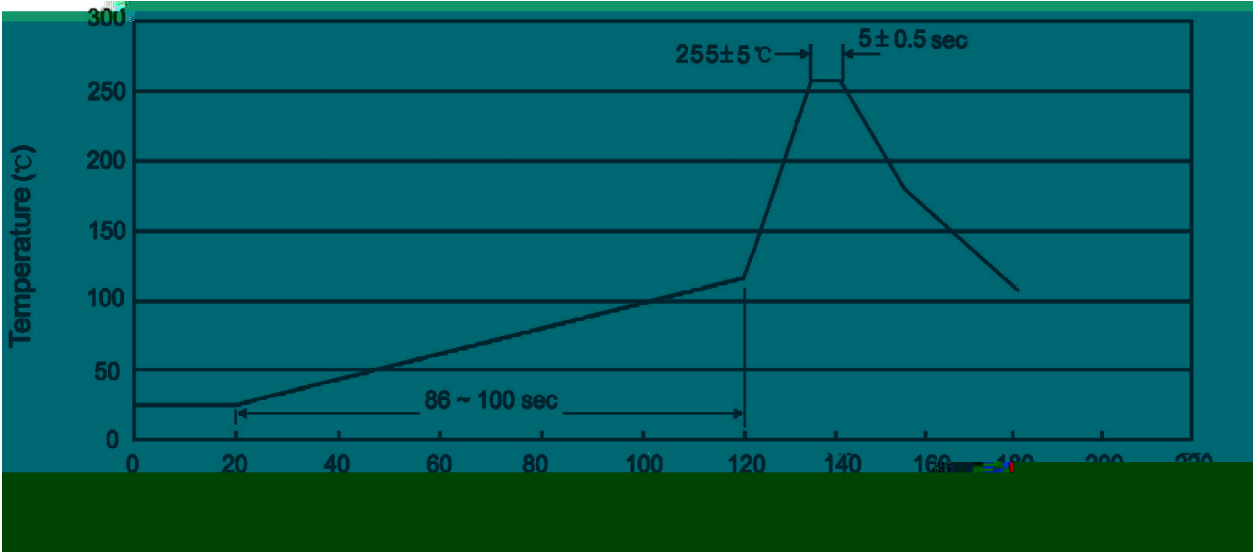
Note:

BR: Company Code.

CA1837: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量		Dimension 包装尺寸 (unit: mm ³)
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	